

ABSTRACT OF THE DISCLOSURE

SA A semiconductor device composed of: a substrate having a
doped semiconductor region, a gate wiring, a lower conductor
structure, an insulating layer overlying the lower structure and
5 having at least one through opening extending to the lower
conductor structure, and an upper conductor structure connected
to the lower conductor structure via the through opening, wherein
at least one of the conductor structures is formed of at least
one layer of a metal, a metal silicide, a metal nitride, a metal
10 carbide or a conductive oxide film, and a metal plating layer
disposed on and adhering to the at least one layer.

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